MJE13003D-P

Preliminary

NPN SILICON TRANSISTOR

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

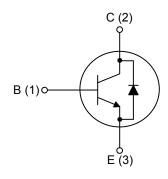
■ DESCRIPTION

The UTC **MJE13003D-P** is a NPN Power Transistor. It is intended to be used in applications requiring medium voltage capability and high switching speeds.

■ FEATURES

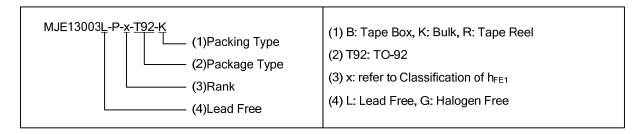
- * Fast-Switching And High Voltage Capability
- * Dynamic Parameters With Low Spread
- * High Reliability
- * Integrated Antiparallel Collector-Emitter Diode

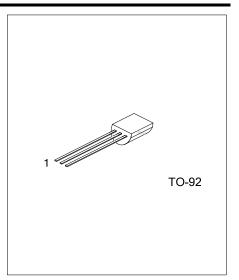
■ INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

Ordering	Daakaga	Pin Assignment			Dooking		
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE13003DL-P-x-T92-B	MJE13003DG-P-x-T92-B	TO-92	E	С	В	Tape Box	
MJE13003DL-P-x-T92-K	MJE13003DG-P-x-T92-K	TO-92	E	С	В	Bulk	
MJE13003DL-P-x-T92-R	MJE13003DG-P-x-T92-R	TO-92	Е	С	В	Tape Reel	





■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	2	SYMBOL	RATINGS	UNIT
Collector- Emitter Voltage (VBE	=0)	$V_{\sf CES}$	700	V
Collector-Emitter Voltage (I _B =0)	$V_{\sf CEO}$	400	V
Emitter-Base Voltage (I _C =0, I _B =	0.75A, t _P <10µS)	V_{EBO}	9	V
Collector Current		Ic	1.5	Α
Collector Peak Current (t _P <5ms)		I _{CM}	3	Α
Base Current		Ι _Β	0.75	Α
Base Peak Current (t _P <5ms)		I _{BM}	1.5	Α
D Discipation	T _A =25°C	0	1.1	W
Power Dissipation	T _C =25°C	P_{D}	1.5	W
Junction Temperature		T_J	150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Emitter-Base Breakdown Voltage		BV_{EBO}	I _E =10mA, I _C =0	9		18	V
Collector-Emitter Sustaining Voltage (Note)		$V_{CEO(SUS)}$	I _C =10mA, I _B =0	450			V
Collector Cut-Off Current		I _{CES}	V _{CE} =700V,V _{BE} =0			1	mA
			I _C =0.5 A, I _B =0.1 A			0.5	V
Collector-Emitter Saturation	on Voltage (Note)	· · · · /	I _C =1 A, I _B =0.25 A			1	V
			I _C =1.5 A, I _B =0.5 A			3	V
Base-Emitter Saturation Voltage (Note)		VDE(0.4T)	I _C =0.5 A, I _B =0.1 A			1	V
			I _C =1 A, I _B =0.25 A			1.2	V
DC Current Gain		h _{FE1}	I _C =0.4A, V _{CE} =5 V	14		57	
		h _{FE2}	I _C =1 A, V _{CE} =5 V	5		30	
Resistive Load	Rise Time	t_R	V _{CC} =125 V, I _C =1 A,			1	μs
	Storage Time	t _S	I _{B1} =0.2 A, I _{B2} =-0.2 A			4	μs
	Fall Time	t_{F}	t _P =25µs			0.7	μs
Inductive Load Storage Time		t_{s}	I_C =1 A, I_{B1} =0.2 A, V_{BE} =-5 V,		0.8		110
		us .	L=50mH, V _{CLAMP} =300V		0.0		μs
Diode Forward Voltage		V_{F}	I _F =0.5 A			1.5	V

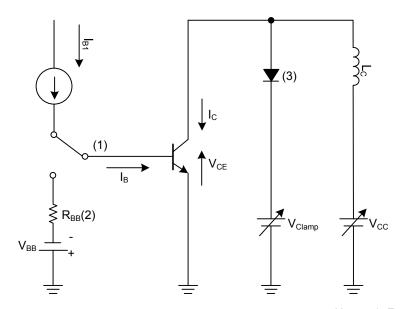
Note: Pulse Test: Pulse duration≤300µs, Duty cycle≤2 %

■ CLASSIFICATION OF h_{FE1}

RANK	Α	В	С	D	E	F	G	Н
RANGE	14 ~ 22	21 ~ 27	26 ~ 32	31 ~ 37	36 ~ 42	41 ~ 47	46 ~ 52	51 ~ 57

■ TEST CIRCURTS

Inductive Load Switching Test Circuit

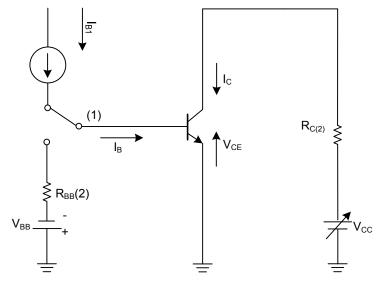


Notes: 1. Fast Electronic Switch

2. Non-Inductive Resistor

3. Fast Recovery Rectifier

Resistive Load Switching Test Circuit



Notes: 1. Fast Electronic Switch

2. Non-Inductive Resistor

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